



Textured nanostructured Mo:BiVO₄ photoanodes with near unity carrier separation and high catalytic efficiency towards oxygen evolution



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Abstract

Improving the intrinsic electronic and catalytic properties of BiVO₄ has remained a challenge and tackling this will help us understand oxygen evolution photocatalysis in general. Here we report BiVO₄ photoanodes with a near unity carrier separation and record catalytic activity towards oxygen evolution. The high carrier separation results in photoanodes with high fill factors making them ideal for current matching in tandem water splitting devices. Crystallographic texturing of the {004} enables efficient hole extraction as well as shows a dramatically lower concentration of in-gap defect states. This study paves the way towards a new approach in designing highly efficient photoanodes for oxygen evolution.

Why BiVO₄?

Pros:

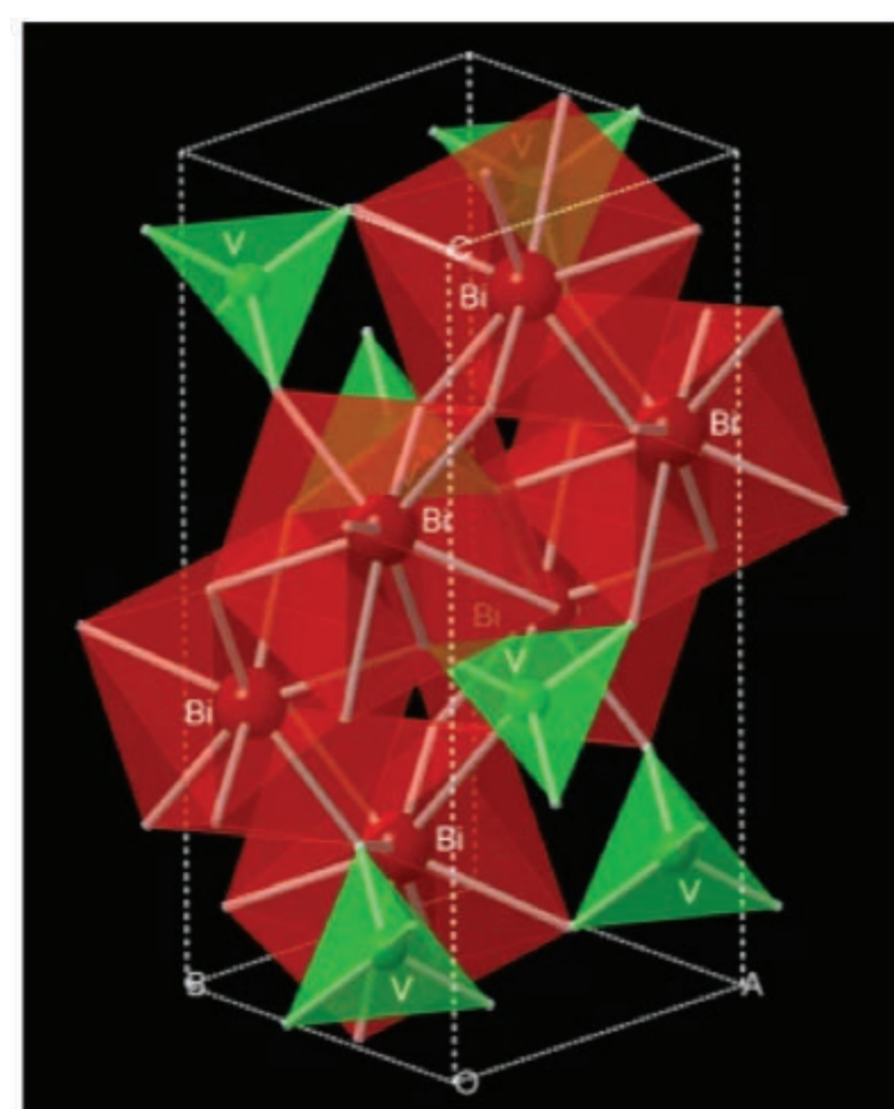
- E_g ~ 2.4 eV, n-type
- α > 20,000 cm⁻¹ for hv > 2.6eV
- E_c ~ 0 V and V_{fb} < 0.2 V vs RHE^[1]
- L_p ~ 100nm^[2]
- earth abundant, nontoxic, cheap



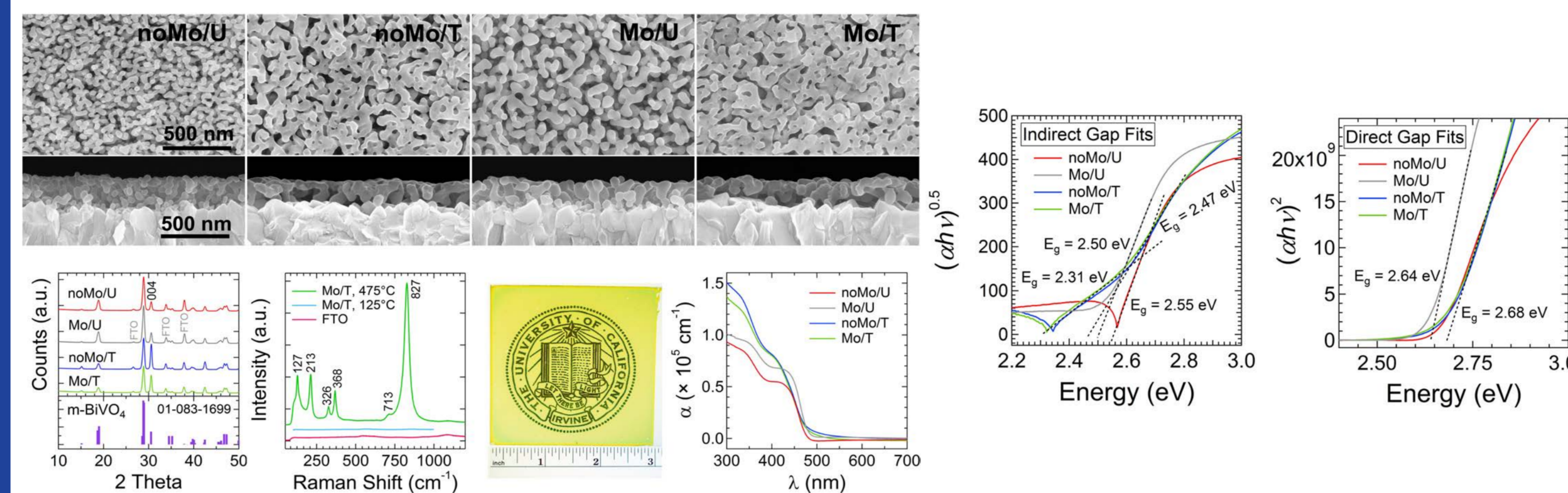
Common yellow pigment

Cons:

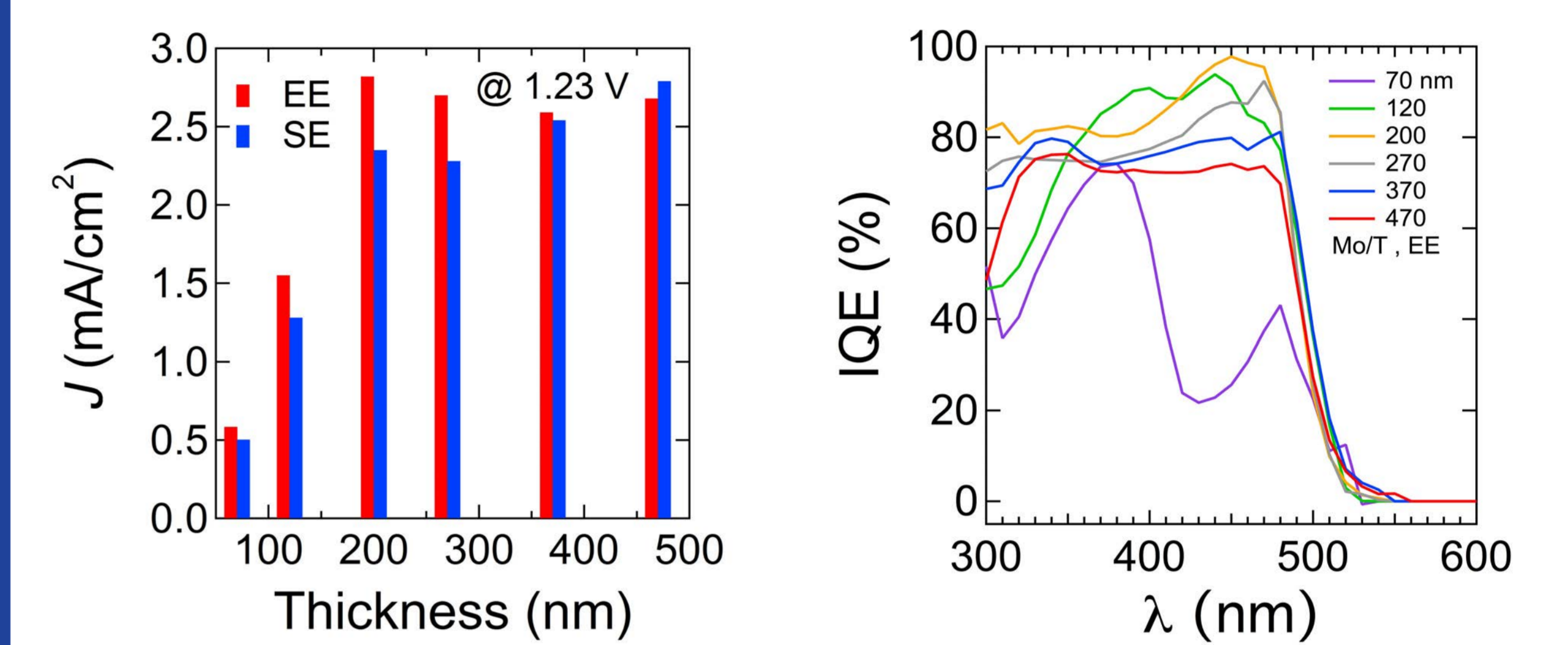
- L_D < α⁻¹ (inadequate transport)
- poor water oxidation kinetics^[3]
- limited stability
- non-optimal E_g (1.8-2.0 eV best)



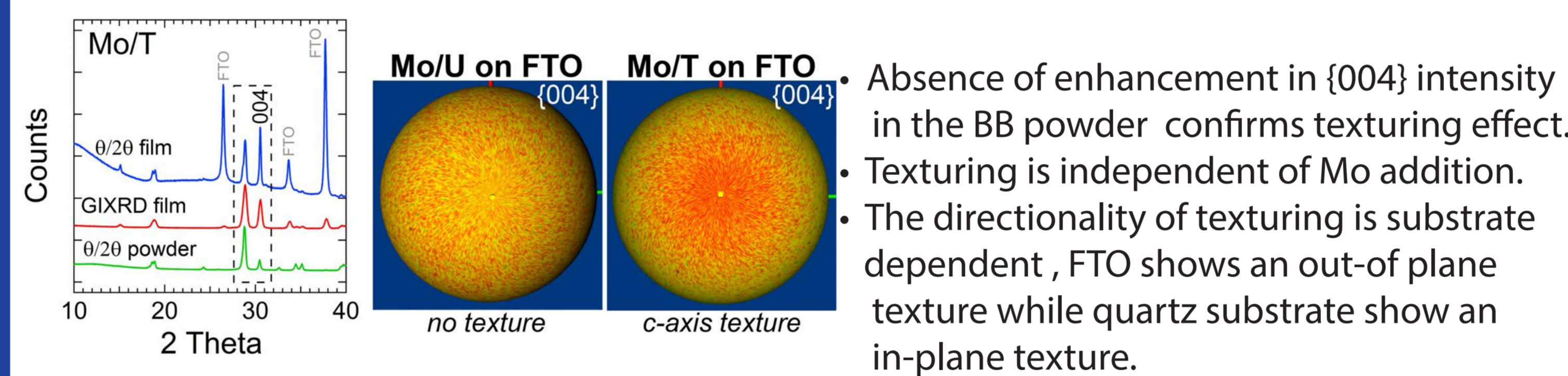
Different flavors of BiVO₄



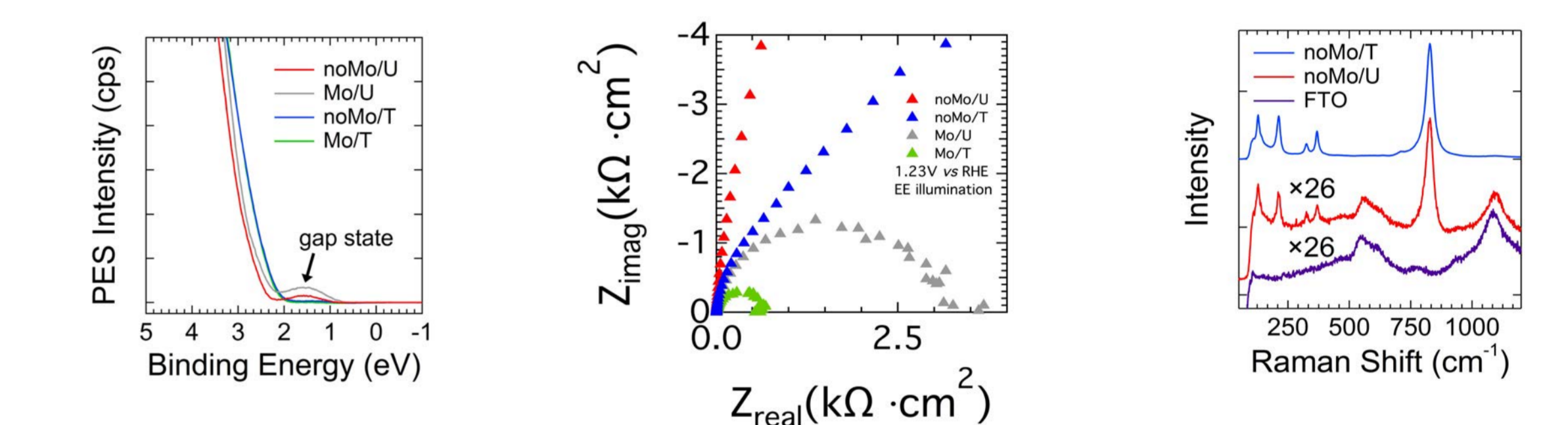
Thickness dependence of photoresponse



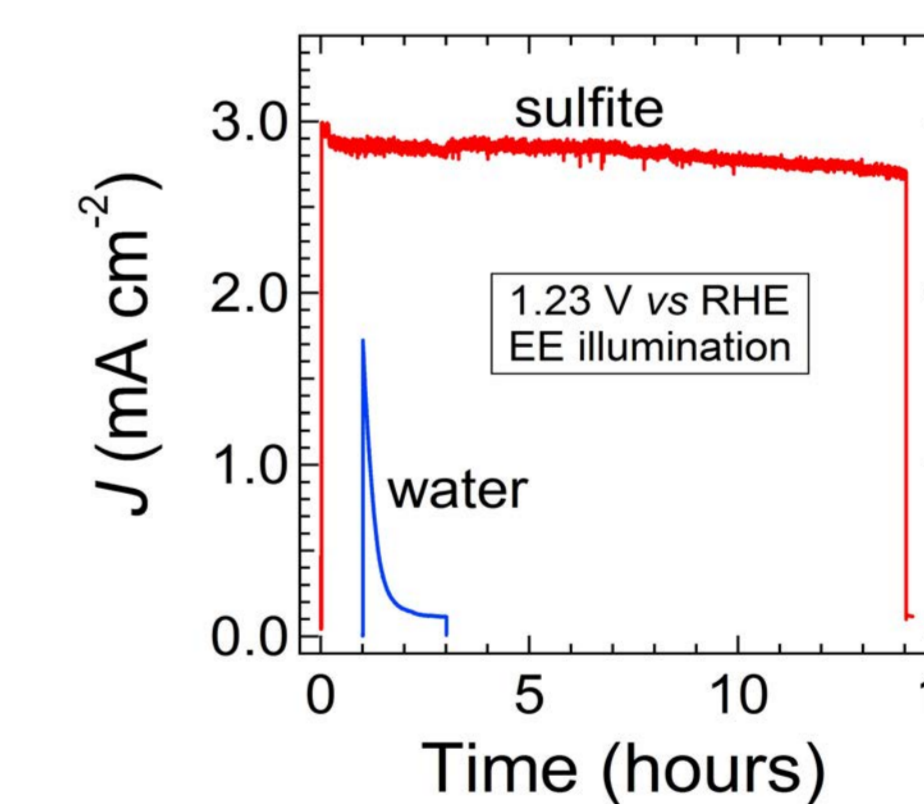
Proof of texturing: In-plane pole figure



Mechanism for enhanced performance and stability



- Untextured films have an in-gap defect state centered around 0.7eV below the conduction band edge.
- In-gap defect states are absent in textured films and have been assigned to oxygen vacancies via hydrogen dosing experiments.
- Impedance spectroscopy was used to confirm low charge transfer resistance.
- The 25x increase in Raman signal for the textured electrodes is attributed to lack of phononic scattering from the in-gap defect states.



- High stability towards sulfite oxidation.
- Water oxidation stability is substantially lower but still best among all BiVO₄-uncatalyzed photoanodes.

Fabrication of Mo/T BiVO₄ photoanodes

dissolve 0.6 mmol Bi(NO₃)₃ in EG, [add 0.012 mmol MoO₂(aacac)₂]

sonicate 5 min

add acetic acid & water

sonicate 10 min

add 0.12 mmol VO(acac)₂

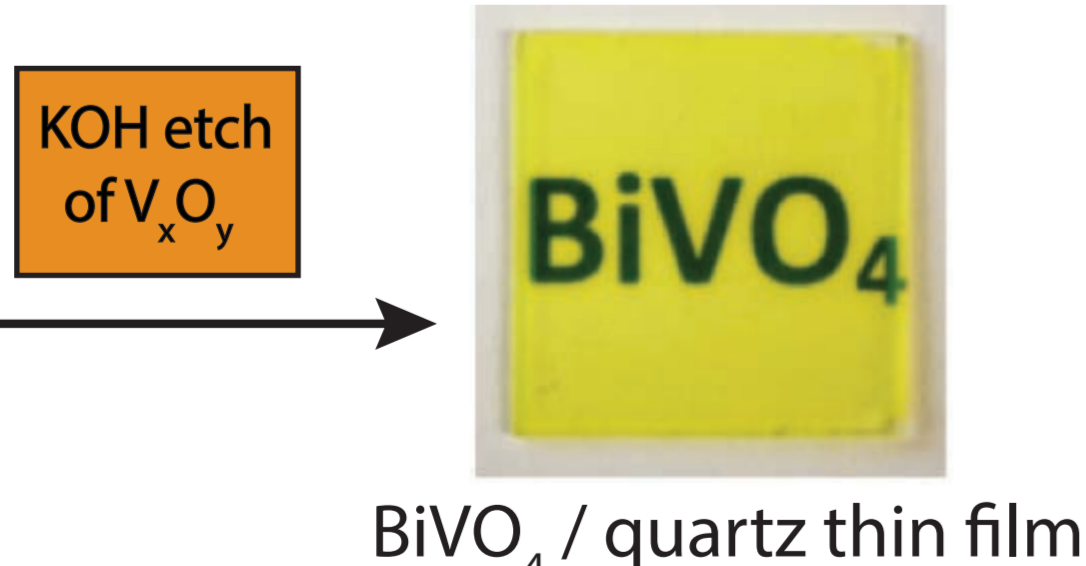
sonicate 10 min

add Pluronic F108 block copolymer

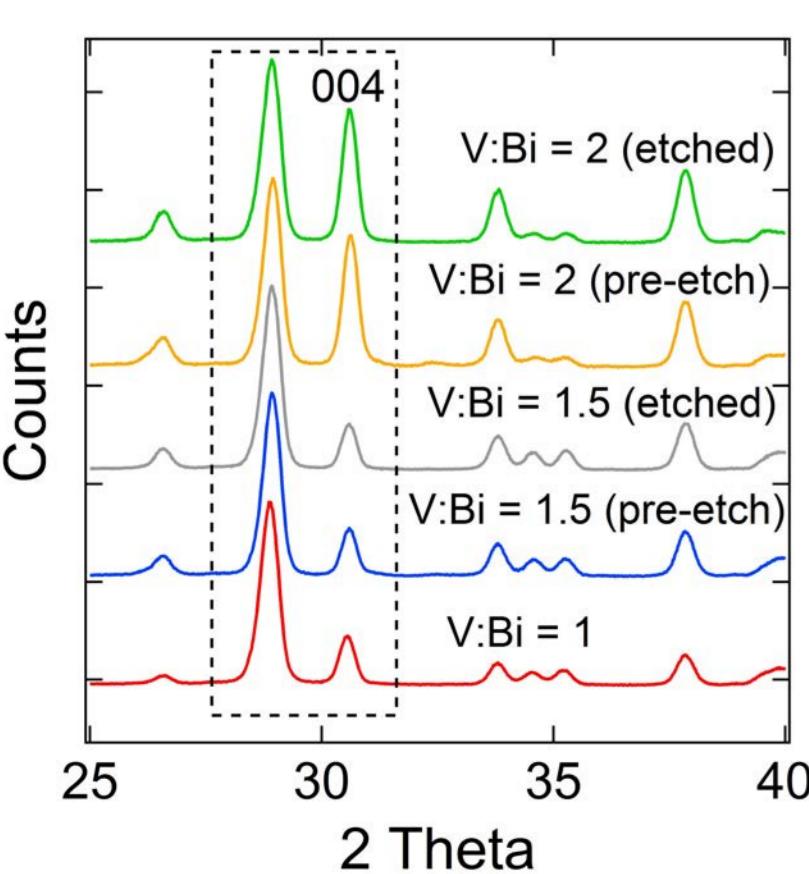
sonicate 30 min

spincoat and anneal (475°C, 15min)

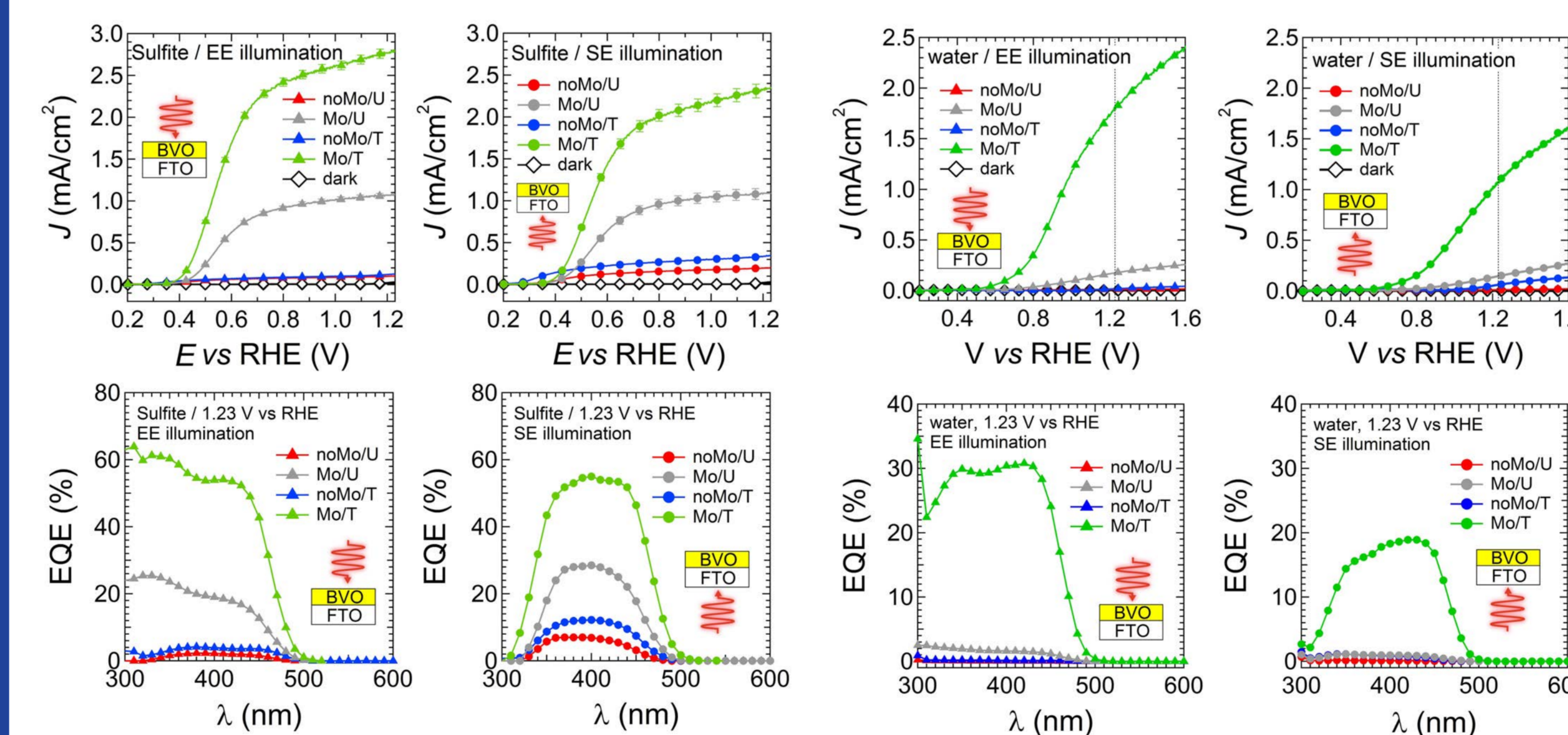
- Single step deposition
- Simple and reproducible over large areas
- High surface area films (nanostructured)
- Robust and optically flat films
- Tunable thickness
- Tunable composition



- Texturing in the films can be controlled by changing the Bi:V precursor ratio in the ink.
- The degree of texturing is thickness dependent.
- The presence of Mo has no effect on the texturing.

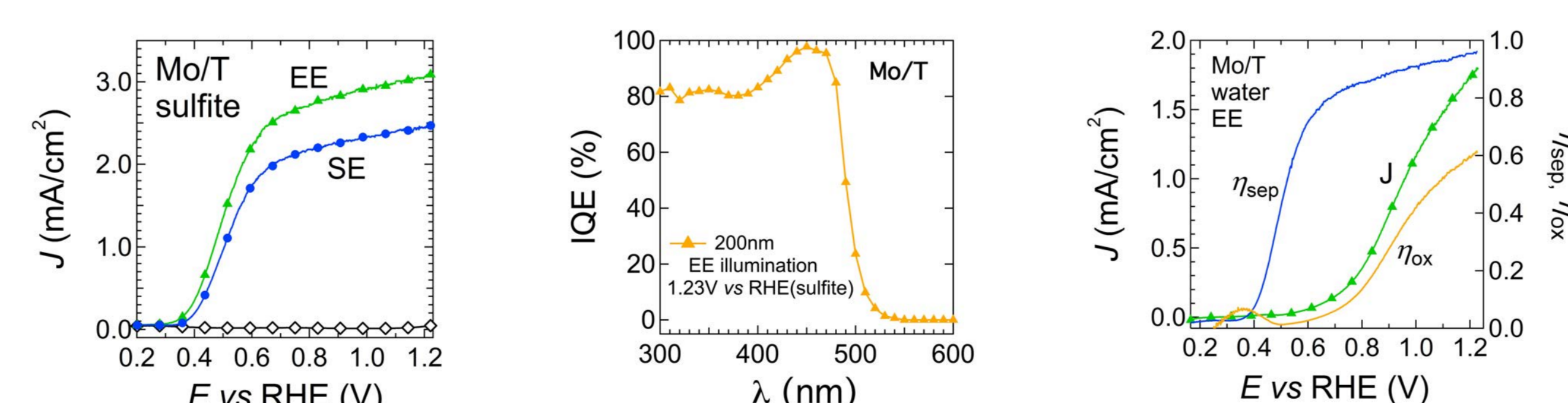


Sulfite vs water oxidation



- Sulfite being a hole scavenger shows higher photoresponse than water oxidation.
- Front-illuminated devices(EE) perform better for both sulfite and water oxidation.

Unity charge extraction and record catalytic activity



- Separation efficiency is high as 80% at low bias conditions (0.6V vs RHE) and nearly 100% at OER.
- IQE for 200 nm Mo/T films rises sharply at band edge and is on an average of 90% above the band edge.

Conclusions and Future Work

- Simultaneous texturing and Mo addition results in superior carrier separation in BiVO₄
- Onset potential for water oxidation is ~ 0.53 V vs RHE which is one of the lowest reported for standalone uncatalysed BiVO₄ emphasizing the sizeable enhancement in the catalytic properties of the photoanode.
- Lower density of in-gap defect states coupled with a lower activation energy for H₂O adsorption on the {004} facet^[4] is the reason for the observed enhancement.
- Future work will be focussed on improving the onset potential for water oxidation in the absence of a catalyst as well as improve the stability towards water oxidation.

References

- [1] Park Y., McDonald K.J., Choi K.S., Chem.Soc.Rev., 2013, 42, 2321-2337.
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